

# Maki Kushimoto

## List of Publications by Year in descending order

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28  
papers

748  
citations

686830

13  
h-index

552369

26  
g-index

28  
all docs

28  
docs citations

28  
times ranked

823  
citing authors

#	ARTICLE	IF	CITATIONS
1	A 271.8 nm deep-ultraviolet laser diode for room temperature operation. Applied Physics Express, 2019, 12, 124003.	1.1	217
2	Correlation between dislocations and leakage current of p-n diodes on a free-standing GaN substrate. Applied Physics Letters, 2018, 112, .	1.5	142
3	Experimental observation of high intrinsic thermal conductivity of AlN. Physical Review Materials, 2020, 4, .	0.9	60
4	On-wafer fabrication of etched-mirror UV-C laser diodes with the ALD-deposited DBR. Applied Physics Letters, 2020, 116, .	1.5	42
5	Design and characterization of a low-optical-loss UV-C laser diode. Japanese Journal of Applied Physics, 2020, 59, 094001.	0.8	31
6	Optically pumped lasing properties of $(1101)$ InGaN/GaN stripe multiquantum wells with ridge cavity structure on patterned (001) Si substrates. Applied Physics Express, 2015, 8, 022702.	1.1	28
7	Space charge profile study of AlGaIn-based p-type distributed polarization doped claddings without impurity doping for UV-C laser diodes. Applied Physics Letters, 2020, 117, .	1.5	26
8	Improving light output power of AlGaIn-based deep-ultraviolet light-emitting diodes by optimizing the optical thickness of p-layers. Applied Physics Express, 2021, 14, 084004.	1.1	26
9	Continuous-wave lasing of AlGaIn-based ultraviolet laser diode at 274.8 nm by current injection. Applied Physics Express, 2022, 15, 041007.	1.1	25
10	m-plane GaN Schottky Barrier Diodes Fabricated With MOVPE Layer on Several Off-angle m-plane GaN Substrates. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700645.	0.8	20
11	Reduction in operating voltage of AlGaIn homojunction tunnel junction deep-UV light-emitting diodes by controlling impurity concentrations. Applied Physics Express, 2021, 14, 084001.	1.1	17
12	Effect of dislocations on the growth of p-type GaN and on the characteristics of p-n diodes. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600837.	0.8	14
13	Facet dependence of leakage current and carrier concentration in m-plane GaN Schottky barrier diode fabricated with MOVPE. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600829.	0.8	14
14	Suppression of Green Luminescence of Mg-implanted GaN by Subsequent Implantation of Fluorine Ions at High Temperature. Physica Status Solidi (B): Basic Research, 2020, 257, 1900554.	0.7	12
15	Impact of heat treatment process on threshold current density in AlGaIn-based deep-ultraviolet laser diodes on AlN substrate. Applied Physics Express, 2021, 14, 051003.	1.1	9
16	Orientation-controlled epitaxial lateral overgrowth of semipolar GaN on Si(001) with a directionally sputtered AlN buffer layer. Journal of Crystal Growth, 2017, 468, 547-551.	0.7	8
17	Interface amorphization in hexagonal boron nitride films on sapphire substrate grown by metalorganic vapor phase epitaxy. Applied Physics Express, 2018, 11, 051002.	1.1	8
18	V-shaped dislocations in a GaN epitaxial layer on GaN substrate. AIP Advances, 2019, 9, .	0.6	8

#	ARTICLE	IF	CITATIONS
19	Sputtered polycrystalline MgZnO/Al reflective electrodes for enhanced light emission in AlGaIn-based homojunction tunnel junction DUV-LED. <i>Applied Physics Express</i> , 2022, 15, 044001.	1.1	7
20	Reduction of Dislocations in GaN on Silicon Substrate Using In Situ Etching. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700387.	0.7	6
21	Structural design optimization of 279 nm wavelength AlGaIn homojunction tunnel junction deep-UV light-emitting diode. <i>Applied Physics Express</i> , 2022, 15, 044003.	1.1	6
22	Fabrication of InGaIn/GaN Multiple Quantum Wells on (111̄,01) GaN. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JC05.	0.8	5
23	Growth of semipolar $(1\bar{1}1)010$ high-indium-content InGaIn quantum wells using InGaIn tilting layer on Si(001). <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FA10.	0.8	4
24	Effect of Annealing on the Electrical and Optical Properties of MgZnO Films Deposited by Radio Frequency Magnetron Sputtering. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1900955.	0.8	4
25	Threshold increase and lasing inhibition due to hexagonal-pyramid-shaped hillocks in AlGaIn-based DUV laser diodes on single-crystal AlN substrate. <i>Japanese Journal of Applied Physics</i> , 2022, 61, 010601.	0.8	4
26	Visualization of depletion layer in AlGaIn homojunction p-n junction. <i>Applied Physics Express</i> , 0, , .	1.1	3
27	Narrow Excitonic Lines in Core-Shell Nanorods With InGaIn/GaN Quantum Wells Intersected by Basal Stacking Faults. <i>Physica Status Solidi (B): Basic Research</i> , 2019, 256, 1800648.	0.7	2
28	Facet dependence of leakage current and carrier concentration in m-plane GaN Schottky barrier diode fabricated with MOVPE ( <i>Phys. Status Solidi A</i> 8 <sup>^</sup> •2017). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1770150.	0.8	0